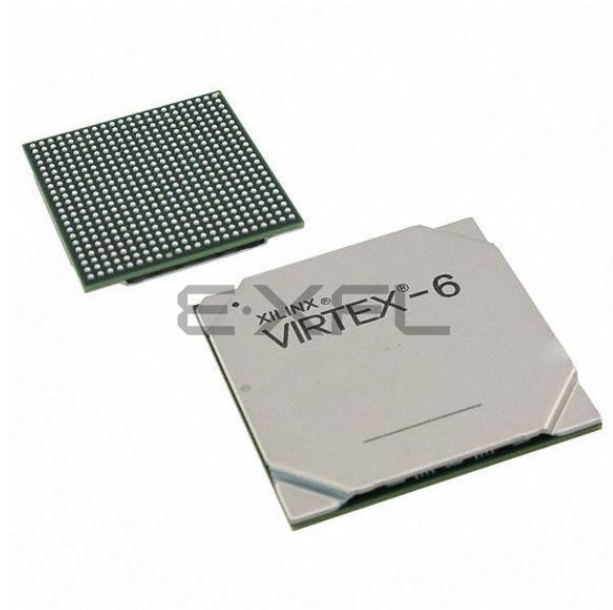




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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	18840
Number of Logic Elements/Cells	241152
Total RAM Bits	15335424
Number of I/O	720
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1759-BBGA, FCBGA
Supplier Device Package	1759-FCBGA (42.5x42.5)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc6vlx240t-1ffg1759i

Table 2: Recommended Operating Conditions

Symbol	Description	Min	Max	Units
V_{CCINT}	Internal supply voltage relative to GND for all devices except -1L devices.	0.95	1.05	V
	For -1L commercial temperature range devices: internal supply voltage relative to GND, $T_j = 0^{\circ}\text{C}$ to $+85^{\circ}\text{C}$	0.87	0.93	V
	For -1L industrial temperature range devices: internal supply voltage relative to GND, $T_j = -40^{\circ}\text{C}$ to $+100^{\circ}\text{C}$	0.91	0.97	V
V_{CCAUX}	Auxiliary supply voltage relative to GND	2.375	2.625	V
$V_{CCO}^{(1)(2)(3)}$	Supply voltage relative to GND	1.14	2.625	V
V_{IN}	2.5V supply voltage relative to GND	GND – 0.20	2.625	V
	2.5V and below supply voltage relative to GND	GND – 0.20	$V_{CCO} + 0.2$	V
$I_{IN}^{(5)}$	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	10	mA
$V_{BATT}^{(6)}$	Battery voltage relative to GND	1.0	2.5	V
$V_{FS}^{(7)}$	External voltage supply for eFUSE programming	2.375	2.625	V
T_j	Junction temperature operating range for commercial (C) temperature devices	0	85	$^{\circ}\text{C}$
	Junction temperature operating range for extended (E) temperature devices	0	100	$^{\circ}\text{C}$
	Junction temperature operating range for industrial (I) temperature devices	–40	100	$^{\circ}\text{C}$
	Junction temperature operating range for military (M) temperature devices	–55	125	$^{\circ}\text{C}$

Notes:

- Configuration data is retained even if V_{CCO} drops to 0V.
- Includes V_{CCO} of 1.2V, 1.5V, 1.8V, and 2.5V.
- The configuration supply voltage V_{CC_CONFIG} is also known as V_{CCO_0} .
- All voltages are relative to ground.
- A total of 100 mA per bank should not be exceeded.
- V_{BATT} is required only when using bitstream encryption. If battery is not used, connect V_{BATT} to either ground or V_{CCAUX} .
- During eFUSE programming, V_{FS} must be within the recommended operating range and $T_j = +15^{\circ}\text{C}$ to $+85^{\circ}\text{C}$. Otherwise, V_{FS} can be connected to GND.

Power-On Power Supply Requirements

Xilinx FPGAs require a certain amount of supply current during power-on to insure proper device initialization. The actual current consumed depends on the power-on sequence and ramp rate of the power supply.

The recommended power-on sequence for Virtex-6 devices is V_{CCINT} , V_{CCAUX} , and V_{CCO} to meet the power-up current requirements listed in Table 5. V_{CCINT} can be powered up or down at any time, but power up current specifications can vary from Table 5. The device will have no physical damage or reliability concerns if V_{CCINT} , V_{CCAUX} , and V_{CCO} sequence cannot be followed.

If the recommended power-up sequence cannot be followed and the I/Os must remain 3-stated throughout configuration, then V_{CCAUX} must be powered prior to V_{CCO} or V_{CCAUX} and V_{CCO} must be powered by the same supply. Similarly, for power-down, the reverse V_{CCAUX} and V_{CCO} sequence is recommended if the I/Os are to remain 3-stated.

The GTH transceiver supplies must be powered using a MGTHAVCC, MGTHAVCCR_X, MGTHAVCCPLL, and MGTHAVTT sequence. There are no sequencing requirement for these supplies with respect to the other FPGA supply voltages. For more detail see Table 27: *GTH Transceiver Power Supply Sequencing*. There are no sequencing requirements for the GTX transceivers power supplies.

Table 5 shows the minimum current, in addition to I_{CCQ} , that are required by Virtex-6 devices for proper power-on and configuration. If the current minimums shown in Table 4 and Table 5 are met, the device powers on after all three supplies have passed through their power-on reset threshold voltages. The FPGA must be configured after applying V_{CCINT} , V_{CCAUX} , and V_{CCO} for the appropriate configuration banks. Once initialized and configured, use the XPE tools to estimate current drain on these supplies.

Table 5: Power-On Current for Virtex-6 Devices

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	Units
	Typ ⁽¹⁾	Typ ⁽¹⁾	Typ ⁽¹⁾	
XC6VLX75T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 10$	$I_{CCOQ} + 30$ mA per bank	mA
XC6VLX130T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 10$	$I_{CCOQ} + 30$ mA per bank	mA
XC6VLX195T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 30$ mA per bank	mA
XC6VLX240T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 30$ mA per bank	mA
XC6VLX365T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 30$ mA per bank	mA
XC6VLX550T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 30$ mA per bank	mA
XC6VLX760	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 30$ mA per bank	mA
XC6VSX315T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 30$ mA per bank	mA
XC6VSX475T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 50$	$I_{CCOQ} + 30$ mA per bank	mA
XC6VHX250T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 30$ mA per bank	mA
XC6VHX255T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 30$ mA per bank	mA
XC6VHX380T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 30$ mA per bank	mA
XC6VHX565T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 30$ mA per bank	mA
XQ6VLX130T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 100$	$I_{CCOQ} + 30$ mA per bank	mA
XQ6VLX240T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 100$	$I_{CCOQ} + 30$ mA per bank	mA
XQ6VLX550T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 100$	$I_{CCOQ} + 30$ mA per bank	mA
XQ6VSX315T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 100$	$I_{CCOQ} + 40$ mA per bank	mA
XQ6VSX475T	See I_{CCINTQ} in Table 4	$I_{CCAUXQ} + 100$	$I_{CCOQ} + 40$ mA per bank	mA

Notes:

- Typical values are specified at nominal voltage, 25°C.
- Use the XPower Estimator (XPE) spreadsheet tool (download at <http://www.xilinx.com/power>) to calculate maximum power-on currents.

HT DC Specifications (HT_25)

Table 8: HT DC Specifications

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OD}	Differential Output Voltage for XC devices	$R_T = 100\ \Omega$ across Q and $\overline{Q}$ signals	480	600	885	mV
	Differential Output Voltage for XQ devices		480	600	930	mV
ΔV_{OD}	Change in V_{OD} Magnitude		-15	—	15	mV
V_{OCM}	Output Common Mode Voltage	$R_T = 100\ \Omega$ across Q and $\overline{Q}$ signals	440	600	760	mV
ΔV_{OCM}	Change in V_{OCM} Magnitude		-15	—	15	mV
V_{ID}	Input Differential Voltage		200	600	1000	mV
ΔV_{ID}	Change in V_{ID} Magnitude		-15	—	15	mV
V_{ICM}	Input Common Mode Voltage		440	600	780	mV
ΔV_{ICM}	Change in V_{ICM} Magnitude		-15	—	15	mV

LVDS DC Specifications (LVDS_25)

Table 9: LVDS DC Specifications

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	$R_T = 100\ \Omega$ across Q and $\overline{Q}$ signals	—	—	1.675	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	$R_T = 100\ \Omega$ across Q and $\overline{Q}$ signals	0.825	—	—	V
V_{ODIFF}	Differential Output Voltage (Q - $\overline{Q}$), Q = High ($\overline{Q}$ - Q), $\overline{Q}$ = High	$R_T = 100\ \Omega$ across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage for XC devices	$R_T = 100\ \Omega$ across Q and $\overline{Q}$ signals	1.075	1.250	1.425	V
	Output Common-Mode Voltage for XQ devices		1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q - $\overline{Q}$), Q = High ($\overline{Q}$ - Q), $\overline{Q}$ = High		100	350	600	mV
V_{ICM}	Input Common-Mode Voltage		0.3	1.2	2.2	V

Extended LVDS DC Specifications (LVDSEXT_25)

Table 10: Extended LVDS DC Specifications

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	$R_T = 100\ \Omega$ across Q and $\overline{Q}$ signals	—	—	1.785	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	$R_T = 100\ \Omega$ across Q and $\overline{Q}$ signals	0.715	—	—	V
V_{ODIFF}	Differential Output Voltage (Q - $\overline{Q}$), Q = High ($\overline{Q}$ - Q), $\overline{Q}$ = High for XC devices	$R_T = 100\ \Omega$ across Q and $\overline{Q}$ signals	350	—	840	mV
	Differential Output Voltage (Q - $\overline{Q}$), Q = High ($\overline{Q}$ - Q), $\overline{Q}$ = High for XQ devices		350	—	850	mV
V_{OCM}	Output Common-Mode Voltage for XC devices	$R_T = 100\ \Omega$ across Q and $\overline{Q}$ signals	1.075	1.250	1.425	V
	Output Common-Mode Voltage for XQ devices		1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q - $\overline{Q}$), Q = High ($\overline{Q}$ - Q), $\overline{Q}$ = High	Common-mode input voltage = 1.25V	100	—	1000	mV
V_{ICM}	Input Common-Mode Voltage	Differential input voltage = ± 350 mV	0.3	1.2	2.2	V

Table 21: GTX Transceiver Reference Clock Switching Characteristics

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range		62.5	–	650	MHz
T_{RCLK}	Reference clock rise time	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time	80% – 20%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle	Transceiver PLL only	45	50	55	%
T_{LOCK}	Clock recovery frequency acquisition time	Initial PLL lock	–	–	1	ms
T_{PHASE}	Clock recovery phase acquisition time	Lock to data after PLL has locked to the reference clock	–	–	200	μ s

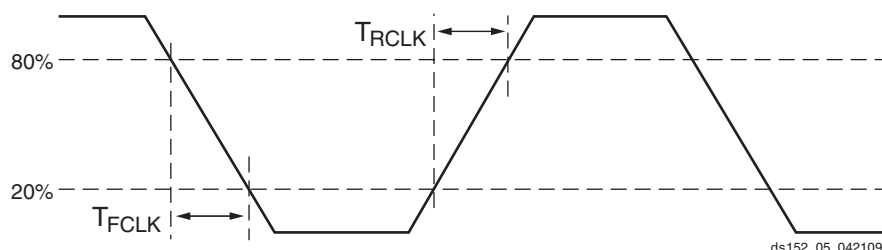


Figure 3: Reference Clock Timing Parameters

Table 22: GTX Transceiver User Clock Switching Characteristics⁽¹⁾

Symbol	Description	Conditions	Speed Grade				Units
			-3	-2	-1	-1L	
F_{TXOUT}	TXOUTCLK maximum frequency	Internal 20-bit data path	330	330	250	250	MHz
		Internal 16-bit data path	412.5	412.5	312.5	250	MHz
F_{RXREC}	RXRECCLK maximum frequency	Internal 20-bit data path	330	330	250	250	MHz
		Internal 16-bit data path	412.5	412.5	312.5	250	MHz
T_{RX}	RXUSRCLK maximum frequency		412.5 ⁽²⁾	412.5 ⁽²⁾	312.5	250	MHz
T_{RX2}	RXUSRCLK2 maximum frequency	1 byte interface	376	376	312.5	250	MHz
		2 byte interface	406.25	406.25	312.5	250	MHz
		4 byte interface	206.25	206.25	156.25	125	MHz
T_{TX}	TXUSRCLK maximum frequency		412.5 ⁽³⁾	412.5 ⁽³⁾	312.5	250	MHz
T_{TX2}	TXUSRCLK2 maximum frequency	1 byte interface	376	376	312.5	250	MHz
		2 byte interface	406.25	406.25	312.5	250	MHz
		4 byte interface	206.25	206.25	156.25	125	MHz

Notes:

1. Clocking must be implemented as described in [UG366: Virtex-6 FPGA GTX Transceivers User Guide](#).
2. 406.25 MHz when the RX elastic buffer is bypassed.
3. 406.25 MHz when the TX buffer is bypassed.

GTH Transceiver Specifications

GTH Transceiver DC Characteristics

Table 25: Absolute Maximum Ratings for GTH Transceivers⁽¹⁾

Symbol	Description	Min	Max	Units
MGTHAVCC	Analog supply voltage for the GTH transmitter, receiver, and common analog circuits	−0.5	1.125	V
MGTHAVCCR _X	Analog supply voltage for the GTH receiver circuits and common analog circuits	−0.5	1.125	V
MGTHAVTT	Analog supply voltage for the GTH transmitter termination circuits	−0.5	1.32	V
MGTHAVCCPLL	Analog supply voltage for the GTH receiver and PLL circuits	−0.5	1.935	V
V _{IN}	Receiver (RXP/RXN) and Transmitter (TXP/TXN) absolute input voltage	−0.5	1.125	V
V _{MGTREFCLK}	Reference clock absolute input voltage	−0.5	1.935	V

Notes:

- Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.

Table 26: Recommended Operating Conditions for GTH Transceivers ⁽¹⁾⁽²⁾

Symbol	Description	Min	Typ	Max	Units
MGTHAVCC	Analog supply voltage for the GTH transmitter, receiver, and common analog circuits	1.075	1.1	1.125	V
MGTHAVCCR _X	Analog supply voltage for the GTH receiver circuits and common analog circuits	1.075	1.1	1.125	V
MGTHAVTT	Analog supply voltage for the GTH transmitter termination circuits	1.140	1.2	1.26	V
MGTHAVCCPLL	Analog supply voltage for the GTH receiver and PLL circuit	1.710	1.8	1.89	V

Notes:

- Each voltage listed requires the filter circuit described in [UG371: Virtex-6 FPGA GTH Transceivers User Guide](#).
- Voltages are specified for the temperature range of T_j = −40°C to +100°C.

Table 27: GTH Transceiver Power Supply Sequencing ⁽¹⁾⁽²⁾⁽³⁾

Symbol	Description	Min	Max	Units
T _{HAVCC2HAVCCR_X}	Maximum time between powering MGTHAVCC to when MGTHAVCCR _X must be powered.	0	5	ms
T _{HAVCCR_X2HAVCCPLL}	Minimum time between powering MGTHAVCCR _X to when MGTHAVCCPLL can be powered.	10	—	μs
T _{HAVCCR_X2HAVTT}	Minimum time between powering MGTHAVCCR _X to when MGTHAVTT can be powered.	10	—	μs

Notes:

- MGTHAVCCR_X must be powered simultaneously or within T_{HAVCC2HAVCCR_X} of MGTHAVCC, but it must not precede MGTHAVCC.
- MGTHAVCC and MGTHAVCCR_X must be powered before MGTHAVCCPLL and MGTHAVTT. This minimum time is defined by T_{HAVCCR_X2HAVCCPLL} and T_{HAVCCR_X2HAVTT}.
- At any time, the condition of MGTHAVCC being present and MGTHAVCCR_X not being present should not occur for more than the maximum T_{HAVCC2HAVCCR_X}.

Figure 4 shows the timing parameters in Table 27.

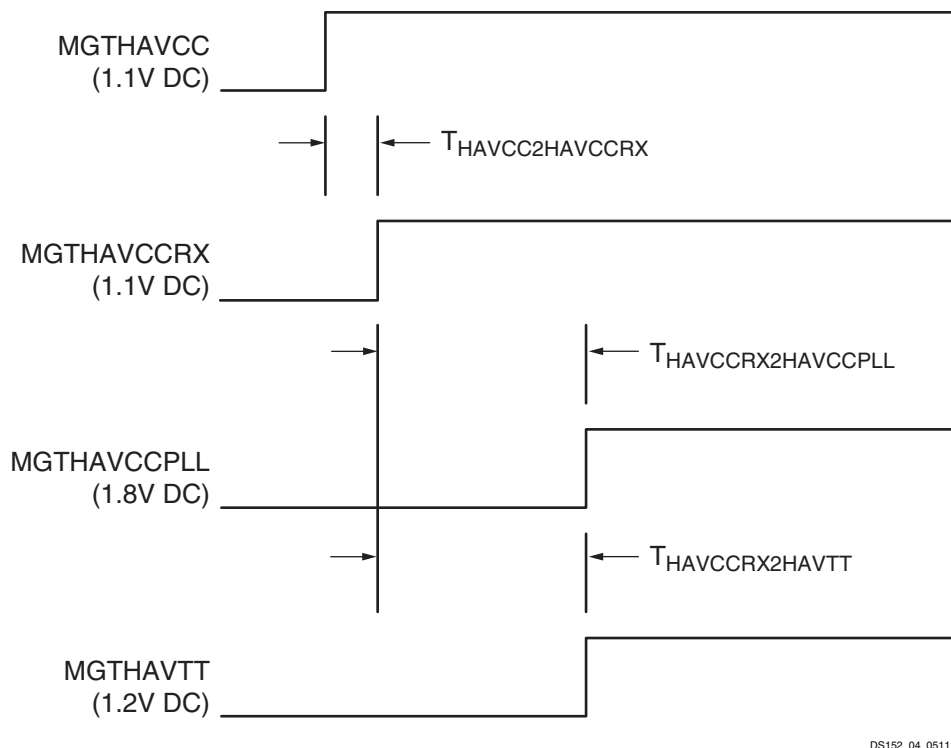


Figure 4: GTH Transceiver Power Supply Power-On Sequencing

Table 28: GTH Transceiver Supply Current

Symbol	Description	Typ ⁽¹⁾	Max	Units
$I_{MGTHAVCC}$	MGTHAVCC supply current for one GTH Quad (4 lanes)	571	Note 2	mA
$I_{MGTHAVCCR}$	MGTHAVCCR supply current for a GTH Quad (4 lanes)	254	Note 2	mA
$I_{MGTHAVTT}$	MGTHAVTT supply current for one GTH Quad (4 lanes)	93	Note 2	mA
$I_{MGTHAVCCPLL}$	MGTHAVCCPLL supply current for one GTH Quad (4 lanes)	219	Note 2	mA
$MGTR_{REF}$	Precision reference resistor for internal calibration termination	1000.0 ± 1% tolerance		Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C, with a 10.3125 Gb/s line rate.
2. Values for currents other than the values specified in this table can be obtained by using the XPower Estimator (XPE) or XPower Analyzer (XPA) tools.

Table 29: GTH Transceiver Quiescent Supply Current⁽¹⁾⁽²⁾

Symbol	Description	Typ ⁽³⁾	Max	Units
$I_{MGTHAVCCQ}$	Quiescent MGTHAVCC Supply Current for one GTH Quad (4 lanes)	65	Note 4	mA
$I_{MGTHAVCCRQ}$	Quiescent MGTHAVCCR Supply Current for one GTH Quad (4 lanes)	17	Note 4	mA
$I_{MGTHAVTTQ}$	Quiescent MGTHAVTT Supply Current for one GTH Quad (4 lanes)	1	Note 4	mA
$I_{MGTHAVCCPLLQ}$	Quiescent MGTHAVCCPLL Supply Current for one GTH Quad (4 lanes)	1	Note 4	mA

Notes:

1. Device powered and unconfigured.
2. GTH transceiver quiescent supply current for an entire device can be calculated by multiplying the values in this table by the number of available GTH transceivers.
3. Typical values are specified at nominal voltage, 25°C.
4. Currents for conditions other than values specified in this table can be obtained by using the XPE or XPA tools.

Integrated Interface Block for PCI Express Designs Switching Characteristics

More information and documentation on solutions for PCI Express designs can be found at:

<http://www.xilinx.com/technology/protocols/pciexpress.htm>

Table 39: Maximum Performance for PCI Express Designs

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
F _{PIPECLK}	Pipe clock maximum frequency	250	250	250	250	MHz
F _{USERCLK}	User clock maximum frequency	500	500	250	250	MHz
F _{DRPCLK}	DRP clock maximum frequency	250	250	250	250	MHz

System Monitor Analog-to-Digital Converter Specification

Table 40: Analog-to-Digital Specifications

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
AV _{DD} = 2.5V ± 5%, V _{REFP} = 1.25V, V _{REFN} = 0V, ADCCLK = 5.2 MHz, T _j = -55°C to 125°C M-Grade, Typical values at T _j = +35°C						
DC Accuracy: All external input channels. Both unipolar and bipolar modes.						
Resolution			10	—	—	Bits
Integral Nonlinearity	INL		—	—	±1	LSBs
Differential Nonlinearity	DNL	No missing codes (T _{MIN} to T _{MAX}) Guaranteed Monotonic	—	—	±0.9	LSBs
Unipolar Offset Error ⁽¹⁾		Uncalibrated	—	±2	±30	LSBs
Bipolar Offset Error ⁽¹⁾		Uncalibrated measured in bipolar mode	—	±2	±30	LSBs
Gain Error		Uncalibrated - External Reference	—	±0.2	±2	%
		Uncalibrated - Internal Reference	—	±2	—	%
Bipolar Gain Error ⁽¹⁾		Uncalibrated - External Reference	—	±0.2	±2	%
		Uncalibrated - Internal Reference	—	±2	—	%
Total Unadjusted Error (Uncalibrated)	TUE	Deviation from ideal transfer function. External 1.25V reference	—	±10	—	LSBs
		Deviation from ideal transfer function. Internal reference	—	±20	—	LSBs
Total Unadjusted Error (Calibrated)	TUE	Deviation from ideal transfer function. External 1.25V reference	—	±1	±2	LSBs
Calibrated Gain Temperature Coefficient		Variation of FS code with temperature	—	±0.01	—	LSB/°C
DC Common-Mode Reject	CMRR _{DC}	V _N = V _{CM} = 0.5V ± 0.5V, V _P - V _N = 100mV	—	70	—	dB
Conversion Rate⁽²⁾						
Conversion Time - Continuous	t _{CONV}	Number of CLK cycles	26	—	32	
Conversion Time - Event	t _{CONV}	Number of CLK cycles	—	—	21	
T/H Acquisition Time	t _{ACQ}	Number of CLK cycles	4	—	—	
DRP Clock Frequency	DCLK	DRP clock frequency	8	—	80	MHz
ADC Clock Frequency	ADCCLK	Derived from DCLK	1	—	5.2	MHz
CLK Duty cycle			40	—	60	%

Table 40: Analog-to-Digital Specifications (Cont'd)

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
Analog Inputs ⁽³⁾						
Dedicated Analog Inputs Input Voltage Range V _P - V _N		Unipolar Operation	0	–	1	Volts
		Bipolar Operation	–0.5	–	+0.5	
		Unipolar Common Mode Range (FS input)	0	–	+0.5	
		Bipolar Common Mode Range (FS input)	+0.5	–	+0.6	
		Bandwidth	–	20	–	MHz
Auxiliary Analog Inputs Input Voltage Range V _{AUXP[0]} /V _{AUXN[0]} to V _{AUXP[15]} /V _{AUXN[15]} T _j = –55°C to 125°C		Unipolar Operation	0	–	1	Volts
		Bipolar Operation	–0.5	–	+0.5	
		Unipolar Common Mode Range (FS input)	0	–	+0.5	
		Bipolar Common Mode Range (FS input)	+0.5	–	+0.6	
		Bandwidth	–	10	–	kHz
Input Leakage Current		A/D not converting, ADCCLK stopped	–	±1.0	–	µA
Input Capacitance			–	10	–	pF
On-chip Supply Monitor Error		V _{CCINT} and V _{CCAUX} with calibration enabled. External 1.25V reference T _j = –55°C to 125°C.	–	–	±1.0	% Reading
		V _{CCINT} and V _{CCAUX} with calibration enabled. Internal reference T _j = –40°C to 100°C. ⁽⁴⁾	–	±2	–	% Reading
On-chip Temperature Monitor Error		T _j = –55°C to +125°C with calibration enabled. External 1.25V reference.	–	–	±4	°C
		T _j = –40°C to +100°C with calibration enabled. Internal reference. ⁽⁴⁾	–	±5	–	°C
External Reference Inputs ⁽⁵⁾						
Positive Reference Input Voltage Range	V _{REFP}	Measured Relative to V _{REFN}	1.20	1.25	1.30	Volts
Negative Reference Input Voltage Range	V _{REFN}	Measured Relative to AGND	–50	0	100	mV
Input current	I _{REF}	ADCCLK = 5.2 MHz	–	–	100	µA
Power Requirements						
Analog Power Supply	AV _{DD}	Measured Relative to AV _{SS}	2.375	2.5	2.625	Volts
Analog Supply Current	AI _{DD}	ADCCLK = 5.2 MHz	–	–	12	mA

Notes:

- Offset errors are removed by enabling the System Monitor automatic gain calibration feature.
- See "System Monitor Timing" in [UG370: Virtex-6 FPGA System Monitor User Guide](#)
- See "Analog Inputs" in [UG370: Virtex-6 FPGA System Monitor User Guide](#) for a detailed description.
- These internal references are not specified over the junction temperature operating range for military (M) temperature devices.
- Any variation in the reference voltage from the nominal $V_{REFP} = 1.25\text{V}$ and $V_{REFN} = 0\text{V}$ will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by $\pm 4\%$ is permitted.

Switching Characteristics

All values represented in this data sheet are based on these speed specifications: v1.17 for -3, -2, and -1; and v1.10 for -1L. Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Production

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to Production before faster speed grades.

All specifications are always representative of worst-case supply voltage and junction temperature conditions.

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device.

Table 42 correlates the current status of each Virtex-6 device on a per speed grade basis.

Table 42: Virtex-6 Device Speed Grade Designations

Device	Speed Grade Designations		
	Advance	Preliminary	Production
XC6VLX75T			-3, -2, -1, -1L
XC6VLX130T			-3, -2, -1, -1L
XC6VLX195T			-3, -2, -1, -1L
XC6VLX240T			-3, -2, -1, -1L
XC6VLX365T			-3, -2, -1, -1L
XC6VLX550T			-2, -1, -1L
XC6VLX760			-2, -1, -1L
XC6VSX315T			-3, -2, -1, -1L
XC6VSX475T			-2, -1, -1L
XC6VHX250T			-3, -2, -1
XC6VHX255T			-3, -2, -1
XC6VHX380T			-3, -2, -1
XC6VHX565T			-2, -1
XQ6VLX130T			-2, -1, -1L
XQ6VLX240T			-2, -1, -1L
XQ6VLX550T			-1, -1L
XQ6VSX315T			-2, -1, -1L
XQ6VSX475T			-1, -1L

Testing of Switching Characteristics

All devices are 100% functionally tested. Internal timing parameters are derived from measuring internal test patterns. Listed below are representative values.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Virtex-6 devices.

Table 44: IOB Switching Characteristics for the Commercial (XC) Virtex-6 Devices (Cont'd)

I/O Standard	T _{IOPI}				T _{IOOP}				T _{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-2	-1	-1L	-3	-2	-1	-1L	-3	-2	-1	-1L	
DIFF_SSTL18_I	0.85	0.94	1.09	1.08	1.47	1.58	1.75	1.73	1.47	1.58	1.75	1.73	ns
DIFF_SSTL18_I_DCI	0.85	0.94	1.09	1.08	1.40	1.51	1.67	1.65	1.40	1.51	1.67	1.65	ns
DIFF_SSTL18_II	0.85	0.94	1.09	1.08	1.39	1.50	1.67	1.66	1.39	1.50	1.67	1.66	ns
DIFF_SSTL18_II_DCI	0.85	0.94	1.09	1.08	1.36	1.47	1.63	1.62	1.36	1.47	1.63	1.62	ns
DIFF_SSTL18_II_T_DCI	0.85	0.94	1.09	1.08	1.40	1.51	1.67	1.65	1.40	1.51	1.67	1.65	ns
DIFF_SSTL15	0.81	0.91	1.06	1.06	1.42	1.54	1.71	1.69	1.42	1.54	1.71	1.69	ns
DIFF_SSTL15_DCI	0.81	0.91	1.06	1.06	1.41	1.52	1.68	1.66	1.41	1.52	1.68	1.66	ns
DIFF_SSTL15_T_DCI	0.81	0.91	1.06	1.06	1.41	1.52	1.68	1.66	1.41	1.52	1.68	1.66	ns

Table 45: IOB Switching Characteristics for the Defense-grade (XQ) Virtex-6 Devices

I/O Standard	T _{IOPI}			T _{IOOP}			T _{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
LVDS_25	0.94	1.09	1.08	1.54	2.16	1.62	1.54	2.16	1.62	ns
LVDSEXT_25	0.94	1.09	1.08	1.65	2.20	1.73	1.65	2.20	1.73	ns
HT_25	0.94	1.09	1.08	1.62	2.20	1.69	1.62	2.20	1.69	ns
BLVDS_25	0.94	1.09	1.08	1.50	3.18	1.65	1.50	3.18	1.65	ns
RSDS_25 (point to point)	0.94	1.09	1.08	1.54	2.22	1.62	1.54	2.22	1.62	ns
HSTL_I	0.91	1.06	1.06	1.56	2.44	1.71	1.56	2.44	1.71	ns
HSTL_II	0.91	1.06	1.06	1.56	2.21	1.72	1.56	2.21	1.72	ns
HSTL_III	0.91	1.06	1.06	1.54	2.50	1.69	1.54	2.50	1.69	ns
HSTL_I_18	0.91	1.06	1.06	1.58	2.43	1.72	1.58	2.43	1.72	ns
HSTL_II_18	0.91	1.06	1.06	1.62	2.30	1.78	1.62	2.30	1.78	ns
HSTL_III_18	0.91	1.06	1.06	1.54	2.49	1.69	1.54	2.49	1.69	ns
SSTL2_I	0.91	1.06	1.06	1.60	2.50	1.74	1.60	2.50	1.74	ns
SSTL2_II	0.91	1.06	1.06	1.54	2.49	1.71	1.54	2.49	1.71	ns
SSTL15	0.91	1.06	1.06	1.54	2.07	1.69	1.54	2.07	1.69	ns
LVC MOS25, Slow, 2 mA	0.57	0.66	0.70	5.46	6.01	5.63	5.46	6.01	5.63	ns
LVC MOS25, Slow, 4 mA	0.57	0.66	0.70	3.49	3.79	3.65	3.49	3.79	3.65	ns
LVC MOS25, Slow, 6 mA	0.57	0.66	0.70	2.81	3.08	2.95	2.81	3.08	2.95	ns
LVC MOS25, Slow, 8 mA	0.57	0.66	0.70	2.41	2.72	2.59	2.41	2.72	2.59	ns
LVC MOS25, Slow, 12 mA	0.57	0.66	0.70	1.95	2.23	2.10	1.95	2.23	2.10	ns
LVC MOS25, Slow, 16 mA	0.57	0.66	0.70	2.05	2.29	2.21	2.05	2.29	2.21	ns
LVC MOS25, Slow, 24 mA	0.57	0.66	0.70	1.82	2.24	1.98	1.82	2.24	1.98	ns
LVC MOS25, Fast, 2 mA	0.57	0.66	0.70	5.49	6.04	5.62	5.49	6.04	5.62	ns
LVC MOS25, Fast, 4 mA	0.57	0.66	0.70	3.50	3.82	3.65	3.50	3.82	3.65	ns
LVC MOS25, Fast, 6 mA	0.57	0.66	0.70	2.73	2.99	2.88	2.73	2.99	2.88	ns
LVC MOS25, Fast, 8 mA	0.57	0.66	0.70	2.33	2.65	2.53	2.33	2.65	2.53	ns
LVC MOS25, Fast, 12 mA	0.57	0.66	0.70	1.88	2.08	2.03	1.88	2.08	2.03	ns

Table 45: IOB Switching Characteristics for the Defense-grade (XQ) Virtex-6 Devices (Cont'd)

I/O Standard	T _{IOPI}			T _{IOOP}			T _{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
LVC MOS25, Fast, 16 mA	0.57	0.66	0.70	1.92	2.15	2.08	1.92	2.15	2.08	ns
LVC MOS25, Fast, 24 mA	0.57	0.66	0.70	1.79	2.15	1.96	1.79	2.15	1.96	ns
LVC MOS18, Slow, 2 mA	0.61	0.71	0.73	4.47	4.87	4.30	4.47	4.87	4.30	ns
LVC MOS18, Slow, 4 mA	0.61	0.71	0.73	2.96	3.21	2.94	2.96	3.21	2.94	ns
LVC MOS18, Slow, 6 mA	0.61	0.71	0.73	2.43	2.64	2.47	2.43	2.64	2.47	ns
LVC MOS18, Slow, 8 mA	0.61	0.71	0.73	2.11	2.41	2.24	2.11	2.41	2.24	ns
LVC MOS18, Slow, 12 mA	0.61	0.71	0.73	1.99	2.30	2.10	1.99	2.30	2.10	ns
LVC MOS18, Slow, 16 mA	0.61	0.71	0.73	1.95	2.30	2.04	1.95	2.30	2.04	ns
LVC MOS18, Fast, 2 mA	0.61	0.71	0.73	4.23	4.57	4.08	4.23	4.57	4.08	ns
LVC MOS18, Fast, 4 mA	0.61	0.71	0.73	2.76	2.97	2.74	2.76	2.97	2.74	ns
LVC MOS18, Fast, 6 mA	0.61	0.71	0.73	2.28	2.46	2.32	2.28	2.46	2.32	ns
LVC MOS18, Fast, 8 mA	0.61	0.71	0.73	1.99	2.34	2.14	1.99	2.34	2.14	ns
LVC MOS18, Fast, 12 mA	0.61	0.71	0.73	1.80	2.19	1.88	1.80	2.19	1.88	ns
LVC MOS18, Fast, 16 mA	0.61	0.71	0.73	1.74	2.18	1.88	1.74	2.18	1.88	ns
LVC MOS15, Slow, 2 mA	0.73	0.85	0.85	3.77	4.29	3.91	3.77	4.29	3.91	ns
LVC MOS15, Slow, 4 mA	0.73	0.85	0.85	2.79	3.10	2.93	2.79	3.10	2.93	ns
LVC MOS15, Slow, 6 mA	0.73	0.85	0.85	2.32	2.68	2.50	2.32	2.68	2.50	ns
LVC MOS15, Slow, 8 mA	0.73	0.85	0.85	1.98	2.29	2.24	1.98	2.29	2.24	ns
LVC MOS15, Slow, 12 mA	0.73	0.85	0.85	1.91	2.23	2.07	1.91	2.23	2.07	ns
LVC MOS15, Slow, 16 mA	0.73	0.85	0.85	1.83	2.23	1.98	1.83	2.23	1.98	ns
LVC MOS15, Fast, 2 mA	0.73	0.85	0.85	3.77	4.28	3.91	3.77	4.28	3.91	ns
LVC MOS15, Fast, 4 mA	0.73	0.85	0.85	2.53	2.78	2.66	2.53	2.78	2.66	ns
LVC MOS15, Fast, 6 mA	0.73	0.85	0.85	2.05	2.42	2.16	2.05	2.42	2.16	ns
LVC MOS15, Fast, 8 mA	0.73	0.85	0.85	1.90	2.20	2.04	1.90	2.20	2.04	ns
LVC MOS15, Fast, 12 mA	0.73	0.85	0.85	1.77	2.11	1.90	1.77	2.11	1.90	ns
LVC MOS15, Fast, 16 mA	0.73	0.85	0.85	1.76	2.11	1.92	1.76	2.11	1.92	ns
LVC MOS12, Slow, 2 mA	0.81	0.93	0.95	3.39	3.75	3.54	3.39	3.75	3.54	ns
LVC MOS12, Slow, 4 mA	0.81	0.93	0.95	2.63	2.93	2.79	2.63	2.93	2.79	ns
LVC MOS12, Slow, 6 mA	0.81	0.93	0.95	2.11	2.67	2.26	2.11	2.67	2.26	ns
LVC MOS12, Slow, 8 mA	0.81	0.93	0.95	2.02	2.25	2.17	2.02	2.25	2.17	ns
LVC MOS12, Fast, 2 mA	0.81	0.93	0.95	2.98	3.39	3.11	2.98	3.39	3.11	ns
LVC MOS12, Fast, 4 mA	0.81	0.93	0.95	2.16	2.70	2.31	2.16	2.70	2.31	ns
LVC MOS12, Fast, 6 mA	0.81	0.93	0.95	1.89	2.34	2.05	1.89	2.34	2.05	ns
LVC MOS12, Fast, 8 mA	0.81	0.93	0.95	1.82	2.10	1.98	1.82	2.10	1.98	ns
LVDCI_25	0.57	0.70	0.70	2.14	2.82	2.26	2.14	2.82	2.26	ns
LVDCI_18	0.61	0.71	0.73	2.23	2.78	2.38	2.23	2.78	2.38	ns
LVDCI_15	0.73	0.85	0.85	2.01	2.75	2.18	2.01	2.75	2.18	ns
LVDCI_DV2_25	0.57	0.70	0.70	1.83	2.37	2.00	1.83	2.37	2.00	ns

Table 48: Output Delay Measurement Methodology (Cont'd)

Description	I/O Standard Attribute	R _{REF} (Ω)	C _{REF} ⁽¹⁾ (pF)	V _{MEAS} (V)	V _{REF} (V)
HT (HyperTransport), 2.5V	LDT_25	100	0	0 ⁽²⁾	0.6
LVPECL (Low-Voltage Positive Emitter-Coupled Logic), 2.5V	LVPECL_25	100	0	0 ⁽²⁾	0
LVDCI/HSLVDCI, 2.5V	LVDCI_25, HSLVDCI_25	1M	0	1.25	0
LVDCI/HSLVDCI, 1.8V	LVDCI_18, HSLVDCI_18	1M	0	0.9	0
LVDCI/HSLVDCI, 1.5V	LVDCI_15, HSLVDCI_15	1M	0	0.75	0
HSTL (High-Speed Transceiver Logic), Class I & II, with DCI	HSTL_I_DCI, HSTL_II_DCI	50	0	V _{REF}	0.75
HSTL, Class III, with DCI	HSTL_III_DCI	50	0	0.9	1.5
HSTL, Class I & II, 1.8V, with DCI	HSTL_I_DCI_18, HSTL_II_DCI_18	50	0	V _{REF}	0.9
HSTL, Class III, 1.8V, with DCI	HSTL_III_DCI_18	50	0	1.1	1.8
SSTL (Stub Series Termini.Logic), Class I & II, 1.8V, with DCI	SSTL18_I_DCI, SSTL18_II_DCI	50	0	V _{REF}	0.9
SSTL, Class I & II, 2.5V, with DCI	SSTL2_I_DCI, SSTL2_II_DCI	50	0	V _{REF}	1.25

Notes:

1. C_{REF} is the capacitance of the probe, nominally 0 pF.
2. The value given is the differential output voltage.

Input/Output Logic Switching Characteristics

Table 49: ILOGIC Switching Characteristics

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
Setup/Hold						
T _{ICE1CK} /T _{ICKCE1}	CE1 pin Setup/Hold with respect to CLK	0.21/ 0.03	0.25/ 0.04	0.27/ 0.04	0.31/ 0.05	ns
T _{ISRCK} /T _{ICKSR}	SR pin Setup/Hold with respect to CLK	0.66/ −0.08	0.78/ −0.08	0.96/ −0.08	1.09/ −0.11	ns
T _{IDOCK} /T _{IOCKD}	D pin Setup/Hold with respect to CLK without Delay	0.07/ 0.41	0.08/ 0.46	0.10/ 0.54	0.11/ 0.64	ns
T _{IDOCKD} /T _{IOCKDD}	DDLY pin Setup/Hold with respect to CLK (using IODELAY)	0.10/ 0.32	0.12/ 0.36	0.14/ 0.42	0.16/ 0.50	ns
Combinatorial						
T _{IDI}	D pin to O pin propagation delay, no Delay	0.15	0.17	0.20	0.23	ns
T _{IDID}	DDLY pin to O pin propagation delay (using IODELAY)	0.19	0.22	0.25	0.28	ns
Sequential Delays						
T _{IDLO}	D pin to Q1 pin using flip-flop as a latch without Delay	0.48	0.54	0.64	0.73	ns
T _{IDLOD}	DDLY pin to Q1 pin using flip-flop as a latch (using IODELAY)	0.52	0.58	0.68	0.78	ns
T _{ICKQ}	CLK to Q outputs	0.54	0.61	0.70	0.93	ns
T _{RQ_ILOGIC}	SR pin to OQ/TQ out	0.85	0.97	1.15	1.32	ns
T _{GSRQ_ILOGIC}	Global Set/Reset to Q outputs	7.60	7.60	10.51	10.51	ns
Set/Reset						
T _{RPW_ILOGIC}	Minimum Pulse Width, SR inputs	0.78	0.95	1.20	1.30	ns, Min

Input Serializer/Deserializer Switching Characteristics

Table 51: ISERDES Switching Characteristics

Symbol	Description	Speed Grade					Units
		-3	-2	-1 (XC)	-1 (XQ)	-1L	
Setup/Hold for Control Lines							
T _{ISCKK_BITSIP} / T _{ISCKC_BITSIP}	BITSLIP pin Setup/Hold with respect to CLKDIV	0.07/ 0.15	0.08/ 0.16	0.09/ 0.17	0.09/ 0.17	0.14/ 0.17	ns
T _{ISCKK_CE} / T _{ISCKC_CE} ⁽²⁾	CE pin Setup/Hold with respect to CLK (for CE1)	0.20/ 0.03	0.25/ 0.04	0.27/ 0.04	0.27/ 0.04	0.31/ 0.05	ns
T _{ISCKK_CE2} / T _{ISCKC_CE2} ⁽²⁾	CE pin Setup/Hold with respect to CLKDIV (for CE2)	0.01/ 0.27	0.01 0.29	0.01/ 0.31	0.01/ 0.31	−0.05/ 0.35	ns
Setup/Hold for Data Lines							
T _{ISDCK_D} / T _{ISCKD_D}	D pin Setup/Hold with respect to CLK	0.07/ 0.08	0.08/ 0.09	0.09/ 0.11	0.09/ 0.11	0.11/ 0.19	ns
T _{ISDCK_DDLY} / T _{ISCKD_DDLY}	DDLY pin Setup/Hold with respect to CLK (using IODELAY) ⁽¹⁾	0.10/ 0.05	0.12/ 0.06	0.14/ 0.07	0.14/ 0.07	0.16/ 0.15	ns
T _{ISDCK_D_DDR} / T _{ISCKD_D_DDR}	D pin Setup/Hold with respect to CLK at DDR mode	0.07/ 0.08	0.08/ 0.09	0.09/ 0.11	0.09/ 0.11	0.11/ 0.19	ns
T _{ISDCK_DDLY_DDR} / T _{ISCKD_DDLY_DDR}	D pin Setup/Hold with respect to CLK at DDR mode (using IODELAY) ⁽¹⁾	0.10/ 0.05	0.12/ 0.06	0.14/ 0.07	0.14/ 0.07	0.16/ 0.15	ns
Sequential Delays							
T _{ISCKO_Q}	CLKDIV to out at Q pin	0.57	0.66	0.75	0.80	0.88	ns
Propagation Delays							
T _{ISDO_DO}	D input to DO output pin	0.19	0.22	0.25	0.25	0.28	ns

Notes:

- Recorded at 0 tap value.
- T_{ISCK_CE2} and T_{ISCK_CE2} are reported as $T_{ISCK_CE} / T_{ISCK_CE}$ in TRACE report.

Input/Output Delay Switching Characteristics

Table 53: Input/Output Delay Switching Characteristics

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
IDELAYCTRL						
T _{DLYCCO_RDY}	Reset to Ready for IDELAYCTRL	3.00	3.00	3.00	3.25	μs
F _{IDELAYCTRL_REF}	REFCLK frequency = 200.0 ⁽¹⁾	200	200	200	200	MHz
	REFCLK frequency = 300.0 ⁽¹⁾	300	300	–	–	MHz
IDELAYCTRL_REF_PRECISION	REFCLK precision	±10	±10	±10	±10	MHz
T _{IDELAYCTRL_RPW}	Minimum Reset pulse width	50.00	50.00	50.00	52.50	ns
IODELAY						
T _{IDELAYRESOLUTION}	IODELAY Chain Delay Resolution	1/(32 x 2 x F _{REF})				ps
T _{IDELAYPAT_JIT}	Pattern dependent period jitter in delay chain for clock pattern. ⁽²⁾	0	0	0	0	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23). ⁽³⁾	±5	±5	±5	±5	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23). ⁽⁴⁾	±9	±9	±9	±9	ps per tap
T _{IODELAY_CLK_MAX}	Maximum frequency of CLK input to IODELAY	500.00	420.00	300.00	300.00	MHz
T _{IODCCK_CE} / T _{IODCKC_CE}	CE pin Setup/Hold with respect to CK	0.45/ –0.09	0.53/ –0.09	0.65/ –0.09	0.84/ –0.14	ns
T _{IODCK_INC} / T _{IODCKC_INC}	INC pin Setup/Hold with respect to CK	0.23/ –0.02	0.27/ –0.01	0.31/ 0.00	0.27/ –0.04	ns
T _{IODCCK_RST} / T _{IODCKC_RST}	RST pin Setup/Hold with respect to CK	0.57/ –0.08	0.62/ –0.08	0.69/ –0.08	0.74/ –0.13	ns
T _{IODDO_T}	TSCONTROL delay to MUXE/MUXF switching and through IODELAY	Note 5	Note 5	Note 5	Note 5	ps
T _{IODDO_IDATAIN}	Propagation delay through IODELAY	Note 5	Note 5	Note 5	Note 5	ps
T _{IODDO_ODATAIN}	Propagation delay through IODELAY	Note 5	Note 5	Note 5	Note 5	ps

Notes:

1. Average Tap Delay at 200 MHz = 78 ps, at 300 MHz = 52 ps.
2. When HIGH_PERFORMANCE mode is set to TRUE or FALSE.
3. When HIGH_PERFORMANCE mode is set to TRUE
4. When HIGH_PERFORMANCE mode is set to FALSE.
5. Delay depends on IDELAY tap setting. See TRACE report for actual values.

CLB Switching Characteristics

Table 54: CLB Switching Characteristics

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
Combinatorial Delays						
T _{ILO}	An – Dn LUT address to A	0.06	0.07	0.07	0.09	ns, Max
	An – Dn LUT address to AMUX/CMUX	0.18	0.20	0.22	0.25	ns, Max
	An – Dn LUT address to BMUX_A	0.28	0.31	0.36	0.40	ns, Max

Table 57: Block RAM and FIFO Switching Characteristics (Cont'd)

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T_{RCKK_WE}/T_{RCKC_WE}	Write Enable (WE) input (Block RAM only)	0.44/ 0.19	0.47/ 0.25	0.52/ 0.35	0.67/ 0.24	ns, Min
$T_{RCKK_WREN}/T_{RCKC_WREN}$	WREN FIFO inputs	0.47/ 0.26	0.50/ 0.27	0.55/ 0.30	0.68/ 0.31	ns, Min
$T_{RCKK_RDEN}/T_{RCKC_RDEN}$	RDEN FIFO inputs	0.46/ 0.26	0.50/ 0.27	0.55/ 0.30	0.67/ 0.31	ns, Min
Reset Delays						
T_{RCO_FLAGS}	Reset RST to FIFO Flags/Pointers ⁽¹⁰⁾	0.90	0.98	1.10	1.23	ns, Max
$T_{RCKK_RSTREG}/T_{RCKC_RSTREG}$	FIFO reset timing ⁽¹¹⁾	0.22/ 0.23	0.24/ 0.24	0.28/ 0.26	0.31/ 0.27	ns, Min
Maximum Frequency						
F_{MAX}	Block RAM in TDP and SDP modes (Write First and No Change modes)	600	540	450	340	MHz
	Block RAM (Read First mode)	525	475	400	275	MHz
	Block RAM (SDP mode) ⁽¹²⁾	525	475	400	275	MHz
$F_{MAX_CASCADE}$	Block RAM Cascade (Write First and No Change modes)	550	490	400	300	MHz
	Block RAM Cascade (Read First mode)	475	425	350	235	MHz
F_{MAX_FIFO}	FIFO in all modes	600	540	450	340	MHz
F_{MAX_ECC}	Block RAM and FIFO in ECC configuration	450	400	325	250	MHz

Notes:

- TRACE will report all of these parameters as T_{RCKO_DO} .
- T_{RCKO_DOR} includes T_{RCKO_DOW} , T_{RCKO_DOPR} , and T_{RCKO_DOPW} as well as the B port equivalent timing parameters.
- These parameters also apply to synchronous FIFO with $DO_REG = 0$.
- T_{RCKO_DO} includes T_{RCKO_DOP} as well as the B port equivalent timing parameters.
- These parameters also apply to multirate (asynchronous) and synchronous FIFO with $DO_REG = 1$.
- T_{RCKO_FLAGS} includes the following parameters: T_{RCKO_AEMPTY} , T_{RCKO_AFULL} , T_{RCKO_EMPTY} , T_{RCKO_FULL} , T_{RCKO_RDERR} , T_{RCKO_WRERR} .
- $T_{RCKO_POINTERS}$ includes both $T_{RCKO_RDCOUNT}$ and $T_{RCKO_WRCOUNT}$.
- The ADDR setup and hold must be met when EN is asserted (even when WE is deasserted). Otherwise, block RAM data corruption is possible.
- T_{RCKO_DI} includes both A and B inputs as well as the parity inputs of A and B.
- T_{RCO_FLAGS} includes the following flags: AEMPTY, AFULL, EMPTY, FULL, RDERR, WRERR, RDCOUNT, and WRCOUNT.
- The FIFO reset must be asserted for at least three positive clock edges.
- When using ISE software v12.4 or later, if the RDADDR_COLLISION_HWCONFIG attribute is set to PERFORMANCE or the block RAM is in single-port operation, then the faster F_{MAX} for WRITE_FIRST/NO_CHANGE modes apply.

Table 62: Regional Clock Switching Characteristics (BUFR) (Cont'd)

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T_{BRDO_O}	Propagation delay from CLR to O	0.69	0.74	0.80	1.12	ns
Maximum Frequency						
$F_{MAX}^{(1)}$	Regional clock tree (BUFR)	500	420	300	300	MHz

Notes:

1. The maximum input frequency to the BUFR is the BUFIO F_{MAX} frequency.

Table 63: Horizontal Clock Buffer Switching Characteristics (BUFH)

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T_{BHCKO_O}	BUFH delay from I to O	0.10	0.11	0.13	0.15	ns
T_{BHCK_CE}/T_{BHCK_CE}	CE pin Setup and Hold	0.04/ 0.04	0.04/ 0.04	0.05/ 0.05	0.04/ 0.04	ns
Maximum Frequency						
F_{MAX}	Horizontal clock buffer (BUFH)	800	750	700	667	MHz

MMCM Switching Characteristics

Table 64: MMCM Specification

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
F_{INMAX}	Maximum Input Clock Frequency ⁽¹⁾	800	750	700	700	MHz
F_{INMIN}	Minimum Input Clock Frequency	10	10	10	10	MHz
$F_{INJITTER}$	Maximum Input Clock Period Jitter	< 20% of clock input period or 1 ns Max				
$F_{INDUTY}^{(2)}$	Allowable Input Duty Cycle: 10—49 MHz	25/75				%
	Allowable Input Duty Cycle: 50—199 MHz	30/70				%
	Allowable Input Duty Cycle: 200—399 MHz	35/65				%
	Allowable Input Duty Cycle: 400—499 MHz	40/60				%
	Allowable Input Duty Cycle: >500 MHz	45/55				%
F_{MIN_PSCLK}	Minimum Dynamic Phase Shift Clock Frequency	0.01	0.01	0.01	0.01	MHz
F_{MAX_PSCLK}	Maximum Dynamic Phase Shift Clock Frequency	550	500	450	450	MHz
F_{VCOMIN}	Minimum MMCM VCO Frequency	600	600	600	600	MHz
F_{VCOMAX}	Maximum MMCM VCO Frequency	1600	1440	1200	1200	MHz
$F_{BANDWIDTH}$	Low MMCM Bandwidth at Typical ⁽³⁾	1.00	1.00	1.00	1.00	MHz
	High MMCM Bandwidth at Typical ⁽³⁾	4.00	4.00	4.00	4.00	MHz
$T_{STATPHAOFFSET}$	Static Phase Offset of the MMCM Outputs ⁽⁴⁾	0.12	0.12	0.12	0.12	ns
$T_{OUTJITTER}$	MMCM Output Jitter ⁽⁵⁾	Note 3				
$T_{OUTDUTY}$	MMCM Output Clock Duty Cycle Precision ⁽⁶⁾	0.15	0.20	0.20	0.20	ns
$T_{LOCKMAX}$	MMCM Maximum Lock Time	100	100	100	100	μs
F_{OUTMAX}	MMCM Maximum Output Frequency	800	750	700	700	MHz
F_{OUTMIN}	MMCM Minimum Output Frequency ⁽⁷⁾⁽⁸⁾	4.69	4.69	4.69	4.69	MHz
$T_{EXTFDVAR}$	External Clock Feedback Variation	< 20% of clock input period or 1 ns Max				

Table 64: MMCM Specification (Cont'd)

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
RST _{MINPULSE}	Minimum Reset Pulse Width	1.5	1.5	1.5	1.5	ns
F _{PFDMAX}	Maximum Frequency at the Phase Frequency Detector with Bandwidth Set to High or Optimized ⁽⁹⁾	550	500	450	450	MHz
	Maximum Frequency at the Phase Frequency Detector with Bandwidth Set to Low	300	300	300	300	MHz
F _{PFDMIN}	Minimum Frequency at the Phase Frequency Detector with Bandwidth Set to High or Optimized	135	135	135	135	MHz
	Minimum Frequency at the Phase Frequency Detector with Bandwidth Set to Low	10	10	10	10	MHz
T _{FBDELAY}	Maximum Delay in the Feedback Path	3 ns Max or one CLKIN cycle				
T _{MMCMCK_PSEN} / T _{MMCMCKD_PSEN}	Setup and Hold of Phase Shift Enable	1.04 0.00	1.04 0.00	1.04 0.00	1.04 0.00	ns
T _{MMCMCK_PINCDEC} / T _{MMCMCKD_PINCDEC}	Setup and Hold of Phase Shift Increment/Decrement	1.04 0.00	1.04 0.00	1.04 0.00	1.04 0.00	ns
T _{MMCMCKO_PSDONE}	Phase Shift Clock-to-Out of PSDONE	0.32	0.34	0.38	0.38	ns

Notes:

1. When DIVCLK_DIVIDE = 3 or 4, F_{INMAX} is 315 MHz.
2. This duty cycle specification does not apply to the GTH_QUAD (GTH) to MMCM connection. The GTH transceivers drive the MMCMs at the following maximum frequencies: 323 MHz for -1 speed grade devices, 350 MHz for -2 speed grade devices, or 350 MHz for -3 speed grade devices.
3. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
4. The static offset is measured between any MMCM outputs with identical phase.
5. Values for this parameter are available in the Clocking Wizard.
See http://www.xilinx.com/products/intellectual-property/clocking_wizard.htm.
6. Includes global clock buffer.
7. Calculated as F_{VCO}/128 assuming output duty cycle is 50%.
8. When CASCADE4_OUT = TRUE, F_{OUTMIN} is 0.036 MHz.
9. In ISE software 12.3 (or earlier versions supporting the Virtex-6 family), the phase frequency detector Optimized bandwidth setting is equivalent to the High bandwidth setting. Starting with ISE software 12.4, the Optimized bandwidth setting is automatically adjusted to Low when the software can determine that the phase frequency detector input is less than 135 MHz.

Table 67: Clock-Capable Clock Input to Output Delay With MMCM

Symbol	Description	Device	Speed Grade				Units
			-3	-2	-1	-1L	
LVCMOS25 Clock-capable Clock Input to Output Delay using Output Flip-Flop, 12mA, Fast Slew Rate, <i>with</i> MMCM.							
T _{ICKOFMMCMCC}	Clock-capable Clock Input and OUTFF <i>with</i> MMCM	XC6VLX75T	2.22	2.38	2.63	2.72	ns
		XC6VLX130T	2.24	2.39	2.65	2.74	ns
		XC6VLX195T	2.24	2.40	2.65	2.75	ns
		XC6VLX240T	2.24	2.40	2.65	2.75	ns
		XC6VLX365T	2.25	2.42	2.65	2.76	ns
		XC6VLX550T	N/A	2.43	2.68	2.80	ns
		XC6VLX760	N/A	2.42	2.69	2.79	ns
		XC6VSX315T	2.23	2.38	2.65	2.73	ns
		XC6VSX475T	N/A	2.30	2.57	2.66	ns
		XC6VHX250T	2.25	2.41	2.67	N/A	ns
		XC6VHX255T	2.35	2.51	2.78	N/A	ns
		XC6VHX380T	2.27	2.43	2.69	N/A	ns
		XC6VHX565T	N/A	2.41	2.68	N/A	ns
		XQ6VLX130T	N/A	2.39	2.65	2.74	ns
		XQ6VLX240T	N/A	2.40	2.65	2.75	ns
		XQ6VLX550T	N/A	N/A	2.68	2.80	ns
		XQ6VSX315T	N/A	2.38	2.65	2.73	ns
		XQ6VSX475T	N/A	N/A	2.57	2.66	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

Table 72: Package Skew

Symbol	Description	Device	Package	Value	Units
T _{PKGSKEW}	Package Skew ⁽¹⁾	XC6VLX75T	FF484	95	ps
			FF784	146	ps
		XC6VLX130T	FF484	95	ps
			FF784	146	ps
			FF1156	165	ps
		XC6VLX195T	FF784	145	ps
			FF1156	182	ps
		XC6VLX240T	FF784	146	ps
			FF1156	182	ps
			FF1759	187	ps
		XC6VLX365T	FF1156	189	ps
			FF1759	184	ps
		XC6VLX550T	FF1759	196	ps
			FF1760	249	ps
		XC6VLX760	FF1760	236	ps
		XC6VSX315T	FF1156	168	ps
			FF1759	190	ps
		XC6VSX475T	FF1156	168	ps
			FF1759	204	ps
		XC6VHX250T	FF1154	166	ps
		XC6VHX255T	FF1155	168	ps
			FF1923	228	ps
		XC6VHX380T	FF1154	159	ps
			FF1155	172	ps
			FF1923	227	ps
			FF1924	220	ps
		XC6VHX565T	FF1923	232	ps
			FF1924	197	ps
		XQ6VLX130T	RF784	146	ps
			RF1156	165	ps
			FFG1156	165	ps
		XQ6VLX240T	RF784	146	ps
			RF1156	182	ps
			FFG1156	182	ps
			RF1759	187	ps
		XQ6VLX550T	RF1759	196	ps
		XQ6VSX315T	RF1156	168	ps
			FFG1156	168	ps
			RF1759	190	ps
		XQ6VSX475T	RF1156	168	ps
			FFG1156	168	ps
			RF1759	204	ps

Notes:

- These values represent the worst-case skew between any two SelectIO resources in the package: shortest flight time to longest flight time from Pad to Ball (7.0 ps per mm).
- Package trace length information is available for these device/package combinations. This information can be used to deskew the package.

Date	Version	Description of Revisions
02/08/11	2.12	Removed note 1 from Table 4 as the larger devices (XC6VLX550T, XC6VLX760, XC6VSX475T, and XC6VHX565T) are now offered in -2I. Updated Table 4 and Table 5 with data for the XC6VHX380T in the FF(G)1154 package. In Table 41 , updated -1L specification for DDR3. Added Note 1 to Table 42 . Moved the XC6VHX380T devices in the FF(G)1154 package to production release in Table 43 using ISE 12.4 software with current speed specifications. Updated description for F_{INDUTY} in Table 64 .
02/25/11	3.0	Designated the data sheet as Preliminary for all devices not already labeled production in Table 42 . Changed the XC6VHX380T devices in all packages to production status in Table 42 and Table 43 . Removed note 1 from Table 42 . Added maximum specifications to Table 25 . Updated $T_{HAVCC2HAVCCRX}$ in Table 27 . Updated the typical values and notes in Table 28 and Table 29 . Added values to Table 30 and Table 31 . In Table 34 , added values for T_{LOCK} and T_{PHASE} . Updated the values in Table 36 and added note 3. Updated Table 37 and added note 4.
03/21/11	3.1	Updated Table 2 including Note 7 . In Table 4 , added Note 3 and -2E, extended temperature range to the XC6VLX550T, XC6VLX760, XC6VSX475T, and XC6VHX380T devices, and added Note 5 for the XC6VHX565T. Updated Table 28 typical values. Updated the description for $F_{IDELAYCTRL_REF}$ in Table 53 . Updated F_{MCCK} in Table 59 .
04/01/11	3.2	Added T_j values for C, E, and I temperature ranges to Table 2 . Updated the I_{CCQ} values in Table 4 . Updated F_{GCLK} in Table 34 . Designated the data sheet as Production for all devices not already labeled production in Table 42 . Changed the XC6VHX255T and XC6VHX565T devices in all packages to production status in Table 42 and Table 43 . This included updates to the Virtex-6 Device Pin-to-Pin Output Parameter Guidelines and Virtex-6 Device Pin-to-Pin Input Parameter Guidelines for these devices. Production speed specifications for these devices are available using the speed specification v1.14 in the ISE 13.1 software update. Updated and added package skew values to Table 72 ; these values are correct with regards to previous production released speed specifications in software. Updated copyright page 1 and Notice of Disclaimer .
12/08/11	3.3	Production release of the Defense-grade XQ devices in Table 42 and Table 43 using ISE v13.3 v1.17 Patch for -2 and -1 speed specifications; and v1.10 for -1L speed specifications. Added the XQ6VLX130T, XQ6VLX240T, XQ6VLX550T, XQ6VSX315T, and XQ6VSX475T to the data sheet which included adding Table 45 . Updated T_j in Table 2 . In Table 40 , updated T_j for most specifications and added Note 4 . Added Note 4 to Table 41 . Added -1(XQ) speed specification columns only to Table 50 , Table 51 , Table 52 , and Table 58 . Updated V_{OD} in Table 8 , V_{OCM} in Table 9 , and V_{OCM} and V_{DIFF} in Table 10 . Updated the Power-On Power Supply Requirements section. In Table 27 , updated maximum specification for $T_{HAVCC2HAVCCRX}$ and added Note 3 . Updated T_j in Table 40 . In Table 41 , increased the DDR LVDS receiver (SPI-4.2) -1 speed grade performance value from 1.0 Gb/s to 1.1 Gb/s. In Table 60 , updated the F_{MAX} to add a separate row for the LX760 device values. The speed specifications in the software tools have always matched these values for the LX760, the data sheet is now correct. Updated the notes for $T_{OUTJITTER}$ in Table 64 .
01/12/12	3.4	Added the temperature range -2E to Note 5 in Table 4 .